

N-Channel Power MOSFET

600V, 10A, 0.75Ω

FEATURES

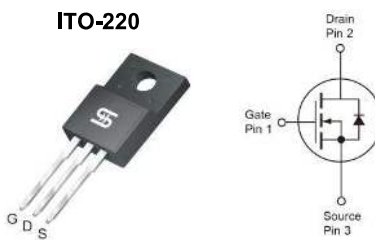
- High power and current handling capability
- Pb-free plating
- Compliant to RoHS Directive 2011/65/EU and in accordance to WEE 2002/96/EC
- Halogen-free according to IEC 61249-2-21 definition

KEY PERFORMANCE PARAMETERS

PARAMETER	VALUE	UNIT
V_{DS}	600	V
$R_{DS(on)}$ (max)	0.75	Ω
Q_g	39	nC

APPLICATION

- Power Supply
- Lighting


ABSOLUTE MAXIMUM RATINGS ($T_A = 25^\circ\text{C}$ unless otherwise noted)

PARAMETER	SYMBOL	Limit	UNIT
Drain-Source Voltage	V_{DS}	600	V
Gate-Source Voltage	V_{GS}	±30	V
Continuous Drain Current ^(Note 1)	I_D	$T_C = 25^\circ\text{C}$	10
		$T_C = 100^\circ\text{C}$	7.7
Pulsed Drain Current ^(Note 2)	I_{DM}	30	A
Total Power Dissipation @ $T_C = 25^\circ\text{C}$	P_{DTOT}	50	W
Single Pulsed Avalanche Energy ^(Note 3)	E_{AS}	37.5	mJ
Single Pulsed Avalanche Current ^(Note 3)	I_{AS}	10	A
Operating Junction and Storage Temperature Range	T_J, T_{STG}	- 55 to +150	°C

THERMAL PERFORMANCE

PARAMETER	SYMBOL	Limit	UNIT
Junction to Case Thermal Resistance	$R_{\theta JC}$	2.5	°C/W
Junction to Ambient Thermal Resistance	$R_{\theta JA}$	62	°C/W

Notes: $R_{\theta JA}$ is the sum of the junction-to-case and case-to-ambient thermal resistances. The case thermal reference is defined at the solder mounting surface of the drain pins. $R_{\theta JA}$ is guaranteed by design while $R_{\theta CA}$ is determined by the user's board design. $R_{\theta JA}$ shown below for single device operation on FR-4 PCB with minimum recommended footprint in still air.

ELECTRICAL SPECIFICATIONS ($T_A = 25^\circ\text{C}$ unless otherwise noted)						
PARAMETER	CONDITIONS	SYMBOL	MIN	TYP	MAX	UNIT
Static (Note 4)						
Drain-Source Breakdown Voltage	$V_{GS} = 0\text{V}, I_D = 250\mu\text{A}$	BV_{DSS}	600	--	--	V
Gate Threshold Voltage	$V_{DS} = V_{GS}, I_D = 250\mu\text{A}$	$V_{GS(TH)}$	2	--	4	V
Gate Body Leakage	$V_{GS} = \pm 30\text{V}, V_{DS} = 0\text{V}$	I_{GSS}	--	--	± 100	nA
Zero Gate Voltage Drain Current	$V_{DS} = 600\text{V}, V_{GS} = 0\text{V}$	I_{DSS}	--	--	10	μA
Drain-Source On-State Resistance	$V_{GS} = 10\text{V}, I_D = 5\text{A}$	$R_{DS(on)}$	--	0.65	0.75	Ω
Dynamic (Note 5)						
Total Gate Charge	$V_{DS} = 380\text{V}, I_D = 10\text{A}, V_{GS} = 10\text{V}$	Q_g	--	39	--	nC
Gate-Source Charge		Q_{gs}	--	9	--	
Gate-Drain Charge		Q_{gd}	--	13	--	
Input Capacitance	$V_{DS} = 25\text{V}, V_{GS} = 0\text{V}, f = 1.0\text{MHz}$	C_{iss}	--	1820	--	pF
Output Capacitance		C_{oss}	--	186	--	
Reverse Transfer Capacitance		C_{rss}		24		
Gate Resistance	$F = 1\text{MHz}, \text{open drain}$	R_g	--	10	--	Ω
Switching (Note 6)						
Turn-On Delay Time	$V_{DD} = 380\text{V}, R_{GEN} = 25\Omega, I_D = 10\text{A}, V_{GS} = 10\text{V},$	$t_{d(on)}$	--	32	--	ns
Turn-On Rise Time		t_r	--	12	--	
Turn-Off Delay Time		$t_{d(off)}$	--	125	--	
Turn-Off Fall Time		t_f	--	27	--	
Source-Drain Diode (Note 4)						
Forward On Voltage	$I_S = 10\text{A}, V_{GS} = 0\text{V}$	V_{SD}	--	--	1.4	V
Reverse Recovery Time	$V_R = 100\text{V}, I_S = 10\text{A}$	t_{rr}	--	363	--	ns
Reverse Recovery Charge	$di_F/dt = 100\text{A}/\mu\text{s}$	Q_{rr}	--	4.5	--	μC

Notes:

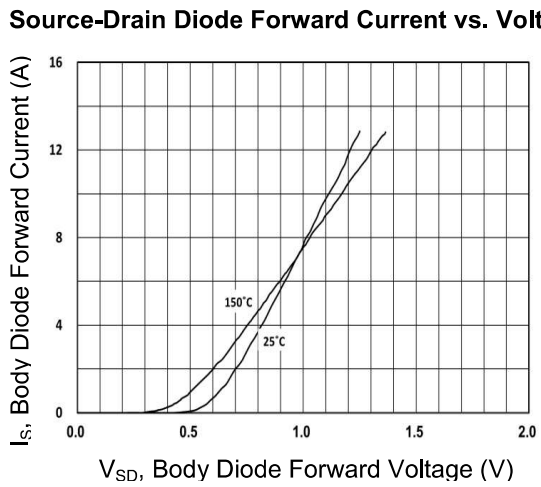
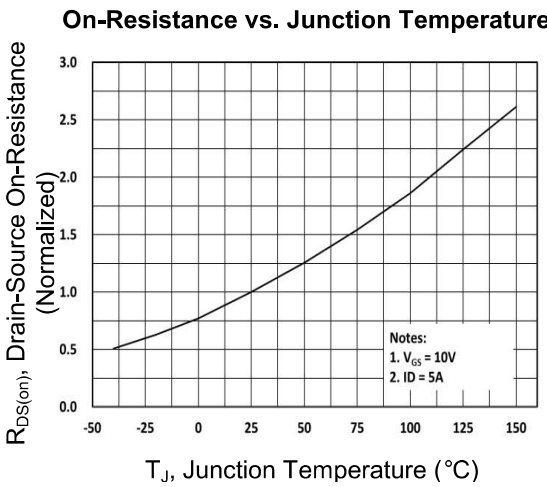
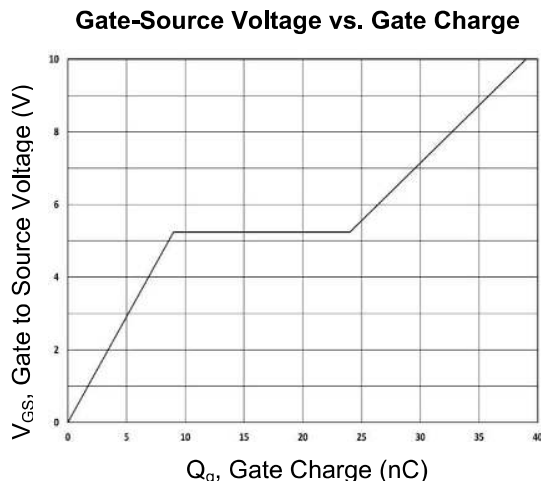
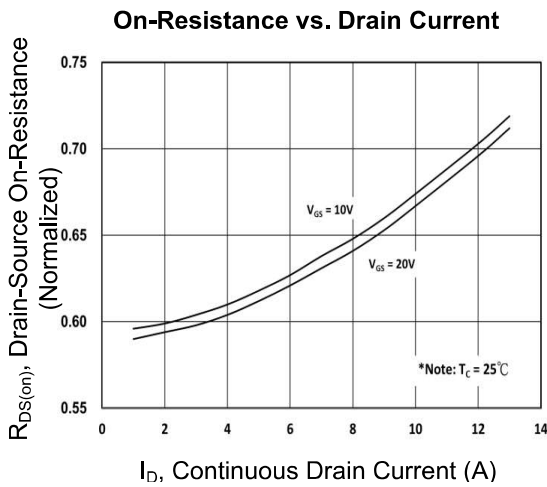
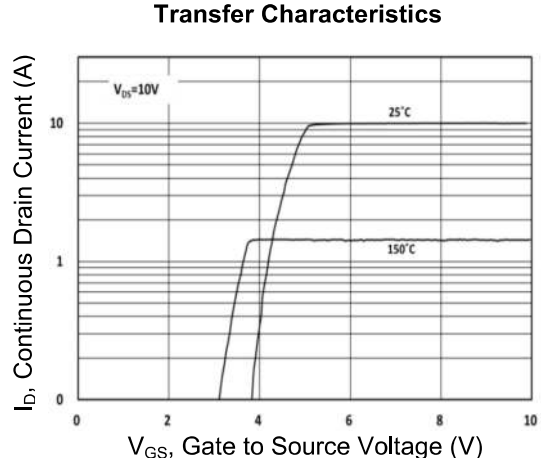
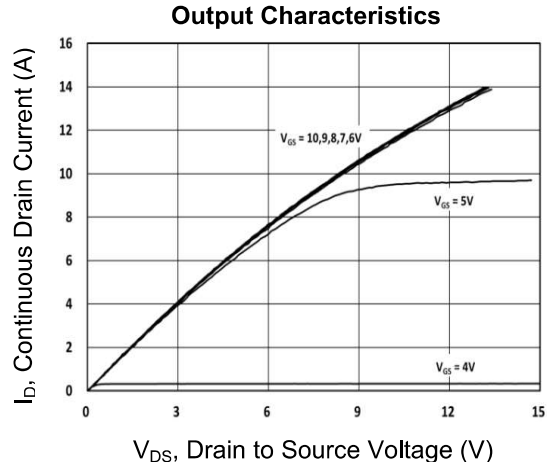
1. Current limited by package.
2. Pulse width limited by the maximum junction temperature.
3. $L = 0.75\text{mH}, I_{AS} = 10\text{A}, V_{DD} = 50\text{V}, R_G = 25\Omega, \text{Starting } T_J = 25^\circ\text{C}$
4. Pulse test: $PW \leq 300\mu\text{s}, \text{duty cycle} \leq 2\%$.
5. For DESIGN AID ONLY, not subject to production testing.
6. Switching time is essentially independent of operating temperature.

ORDERING INFORMATION

PART NO.	PACKAGE	PACKING
TSM10NB60CI C0G	ITO-220	50pcs/Tube

CHARACTERISTICS CURVES

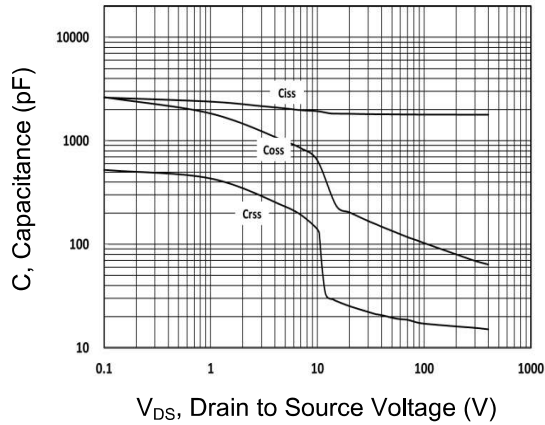
($T_C = 25^\circ\text{C}$ unless otherwise noted)



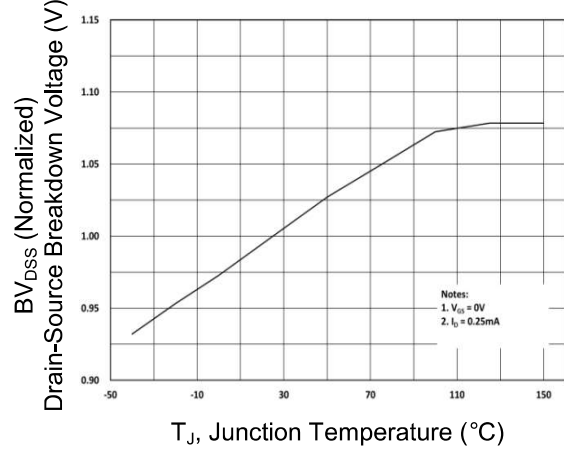
CHARACTERISTICS CURVES

($T_C = 25^\circ\text{C}$ unless otherwise noted)

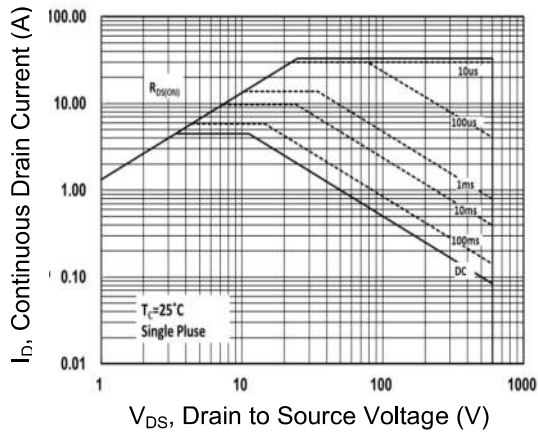
Capacitance vs. Drain-Source Voltage



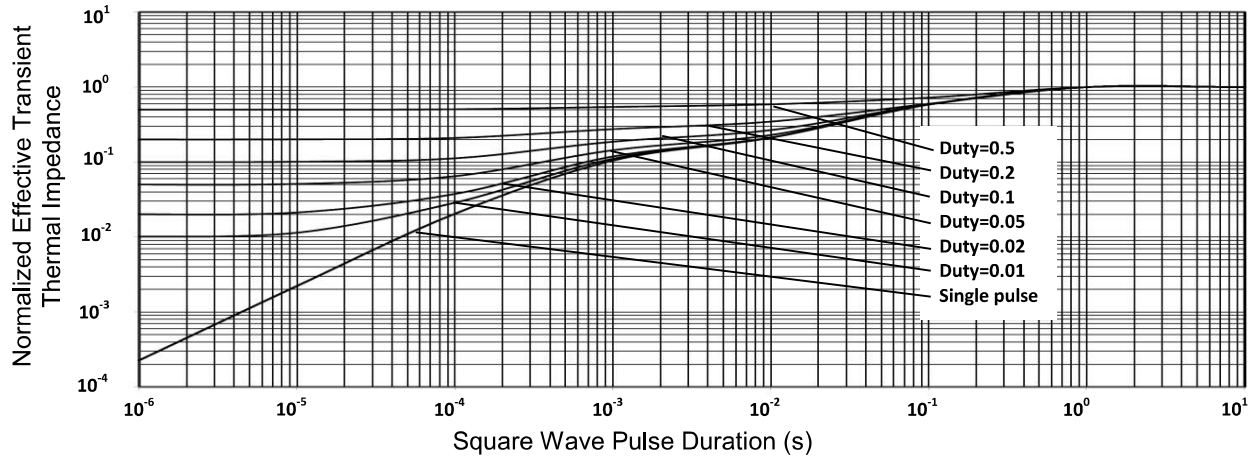
BV_{DSS} vs. Junction Temperature



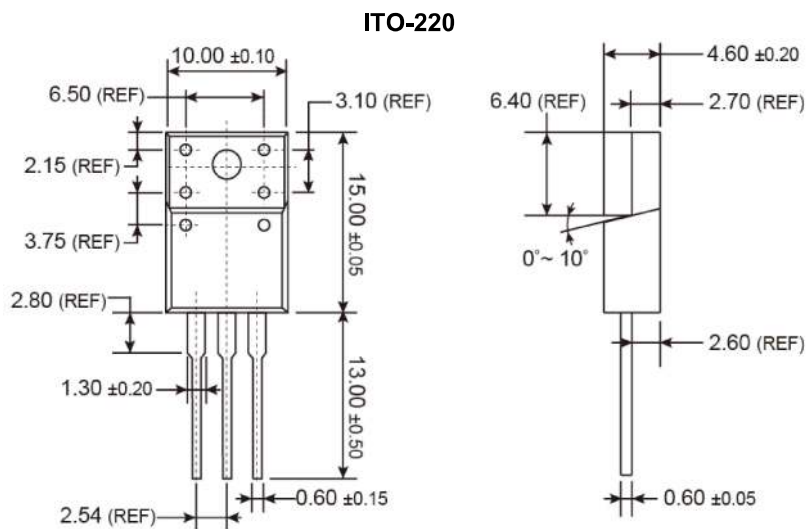
Maximum Safe Operating Area (ITO-220)



Normalized Thermal Transient Impedance, Junction-to-Case (ITO-220)



PACKAGE OUTLINE DIMENSIONS (Unit: Millimeters)



MARKING DIAGRAM



- G** = Halogen Free
- Y** = Year Code
- WW** = Week Code (01~52)
- F** = Factory Code

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